Ordering number: EN 4765

SANYO

No.4765

2SC4919

NPN Epitaxial Planar Silicon Transistor

Muting Circuit Applications

Features

- Very small-sized package permitting 2SC4919-applied sets to be made smaller and slimmer.
- Small output capacitance.
- Low collector-to-emitter saturation voltage.
- Small ON resistance.

Absolute Maximum Ratings at Ta = 25°C

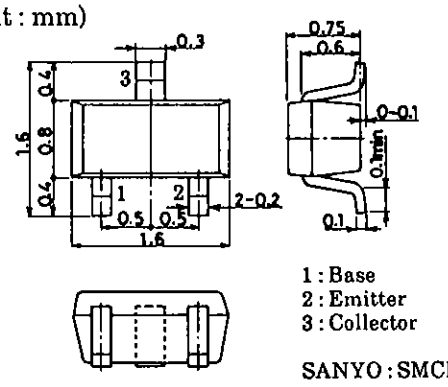
			unit
Collector-to-Base Voltage	V_{CBO}	25	V
Collector-to-Emitter Voltage	V_{CEO}	15	V
Emitter-to-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	100	mA
Collector Current (Pulse)	I_{CP}	200	mA
Base Current	I_B	20	mA
Collector Dissipation	P_C	150	mW
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	−55 to +150	°C

Electrical Characteristics at Ta = 25°C

			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	V_{CB} = 15V, I_E = 0			0.1	μA
Emitter Cutoff Current	I_{EBO}	V_{EB} = 4V, I_C = 0			0.1	μA
DC Current Gain	h_{FE}	V_{CE} = 2V, I_C = 5mA	800		3200	
Gain-Bandwidth Product	f_T	V_{CE} = 5V, I_C = 10mA		240		MHz
Output Capacitance	Cob	V_{CB} = 10V, f = 1MHz		1.4		pF
C-E Saturation Voltage	$V_{CE(sat)}$	I_C = 10mA, I_B = 1mA		14	30	mV
B-E Saturation Voltage	$V_{BE(sat)}$	I_C = 10mA, I_B = 1mA		0.74	1.1	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	I_C = 10μA, I_E = 0	25			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	I_C = 1mA, R_{BE} = ∞	15			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	I_E = 10μA, I_C = 0	5			V
ON Resistance	Ron	I_B = 3mA, f = 1MHz		0.9		Ω

Marking : DA

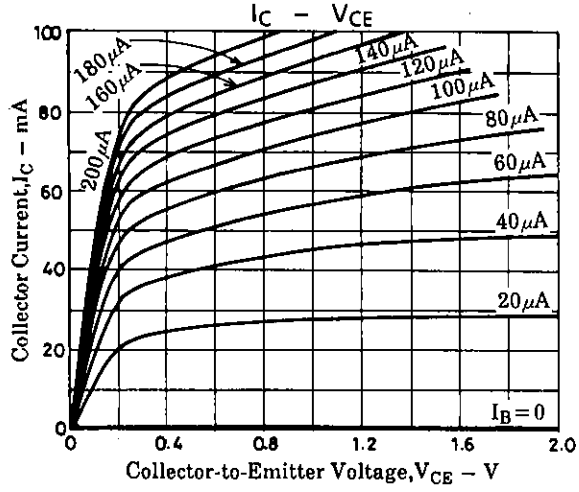
Package Dimensions 2106A
(unit : mm)



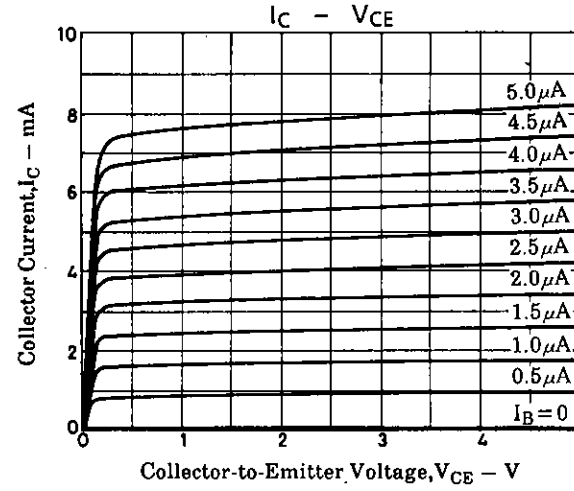
1 : Base
2 : Emitter
3 : Collector

SANYO : SMCP

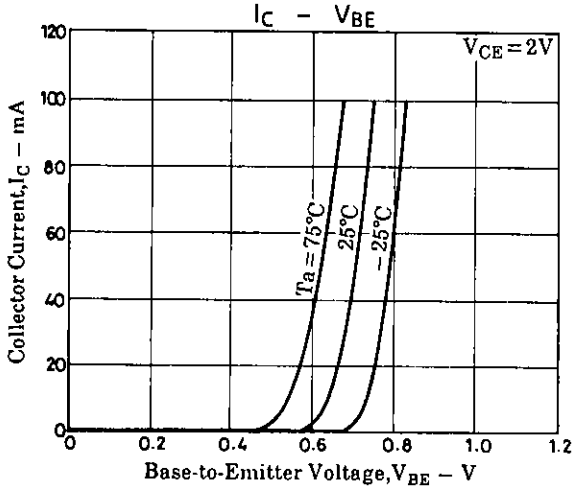
I_C – V_{CE}



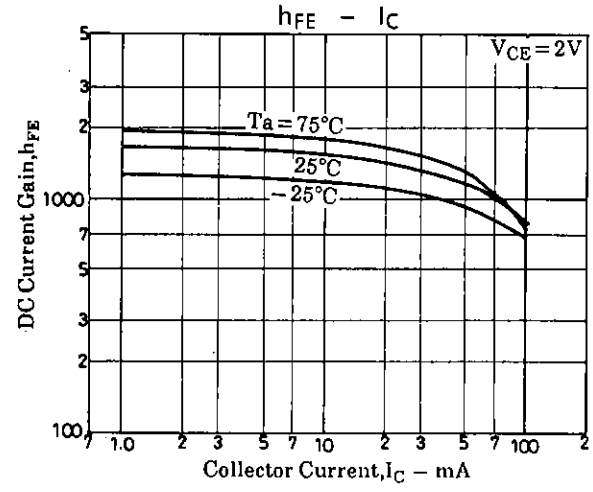
I_C – V_{CE}



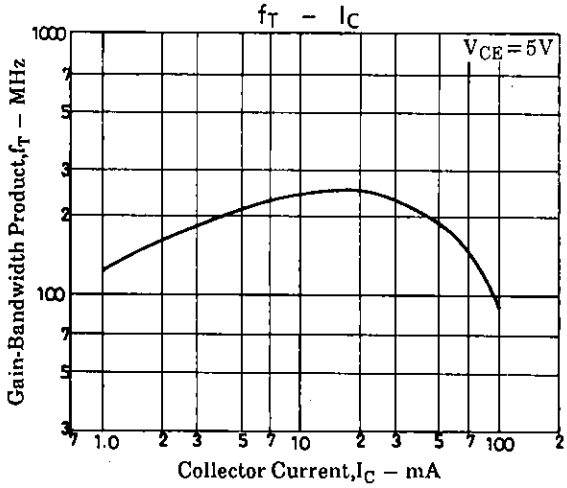
I_C – V_{BE}



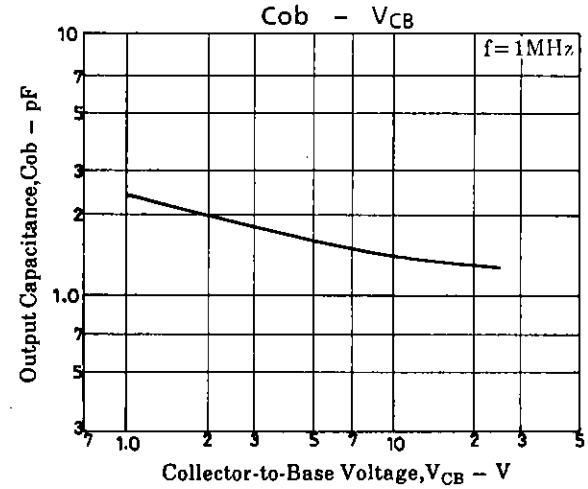
h_{FE} – I_C



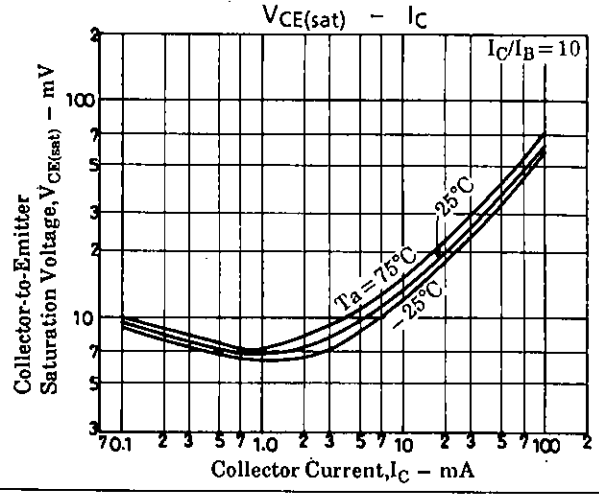
f_T – I_C



Cob – V_{CB}



$V_{CE(sat)}$ – I_C



$V_{BE(sat)}$ – I_C